

Superconductivity in pure and electron doped MgB_2 : Transport properties and pressure effects

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The normal state and superconducting properties of MgB_2 and $Mg_{1-x}Al_xB_2$ are discussed based on structural, transport, and high-pressure experiments. The positive Seebeck coefficient and its linear temperature dependence for $T_c < T < 160$ K provide evidence that the low-temperature transport in MgB_2 is due to hole-like metallic carriers. Structural and transport data show the important role of defects as indicated by the correlation of T_c , the residual resistance ratio, and the microstrain extracted from x-ray spectra. The decrease of T_c with hydrostatic pressure is well explained by the strong-coupling BCS theory. The large scatter of the pressure coefficients of T_c for different MgB_2 samples, however, cannot be explained within this theory. We speculate that pressure may increase the defect density, particularly in samples with large initial defect concentration.

A. Introduction

The discovery of superconductivity at 40 K in MgB_2 by Nagamatsu et al.¹ has initiated a tremendous amount of experimental and theoretical work (for a review see Bueza et al.²). MgB_2 appears to be electrically three dimensional and its grain boundaries have a far less detrimental effect on the superconducting current. The low magnetic anisotropy, the large coherence length, and the high critical current densities in magnetic fields (as compared e.g. to the cuprate superconductors) recommend this compound for device-related applications. The low costs of producing bulk ceramics, thin films, tapes, and wires further reveal the huge potential this compound may have in the near future. MgB_2 crystallizes in the hexagonal AlB_2 structure. The honeycomb-like boron layers are separated by the magnesium ions. In analogy to the graphite lattice MgB_2 may be considered as a completely intercalated graphite structure. Early band structure calculations³ have shown that Mg substantially donates charges into the boron layers and that the electronic bands at the Fermi energy derive mainly from the boron p -bands. Thereby, the Fermi surface displays sheets of hole-like as well as electron-like character. The electrical transport properties in the normal state are sufficiently well described by the Bloch-Grüneisen law of normal metals. The temperature dependence of the resistivity follows a power law with exponents between 2 and 3^{4,5} indicating that the temperature dependent scattering process is the electron-phonon scattering. For a simple binary compound T_c appears to be unusually large. Therefore, the mechanism of superconductivity has been a matter of discussion and different models have been proposed^{3,6}. Within the BCS model the high T_c may be explained by the relatively large energy of the boron phonon modes due to the low mass of the boron ions and a strong electron-phonon interaction (strong coupling limit, coupling constant λ). The phonon-mediated mechanism is supported by a number of experimental results, notably the observed isotope effects⁷, tunnelling measurements of the superconducting gap,⁸⁻¹⁰ and estimates of the electron-phonon coupling constant ($\lambda \approx 0.7...0.9$) from specific heat¹¹ and phonon density-of-states measurements.¹² Calculations of the electronic and phononic structures^{3,13-16} have shown that the bond stretching modes of the boron couple strongly to the $p_{x,y}$ electronic bands and the electron-phonon coupling parameter was estimated between 0.7 and 0.9, lending further support to the strong coupling BCS theory. In contrast to the BCS theory, Hirsch⁶ has proposed an alternative model where superconductivity in MgB_2 is driven by the pairing of dressed holes. In fact, indications for hole-type conduction in the normal state originally found in the positive thermoelectric power¹⁷ were confirmed by Hall effect measurements and analogies to high- T_c cuprate superconductors have been discussed.¹⁸ However, one of the main predictions of this model, an increase of T_c with pressure, could not be confirmed by early high-pressure experiments.^{17,19} Soon after the discovery of superconductivity in pure MgB_2 attempts have been made to raise T_c by substituting the elements Mg or B by ions of different size and/or valency (e.g. Al, Li, C, Cu, Be, Na, Zn, Mn, Si, Co, Ni, Fe). No increase of T_c has been reported so far. However, substitutions are a tool to modify certain microscopic parameters such as lattice constants and carrier densities and may facilitate the understanding of the microscopic mechanisms in the normal and superconducting states. Based on the theory of normal metals we discuss the transport properties, especially the thermoelectric effect, of MgB_2 and $Mg_{1-x}Al_xB_2$ (Section B). In Section C the influence of defects on T_c , lattice

constants, and electronic transport is investigated. Pressure effects on the superconducting transition temperature are discussed in the final Section.

B. Thermoelectric Transport Properties of MgB_2 and $Mg_{1-x}Al_xB_2$

Electrical transport measurements of MgB_2 have been reported in a large number of papers. The resistivity roughly follows a power law,

$$\rho(T) = \rho_0 + AT^n \quad (1)$$

with an exponent n between 2 and 3. Equation (1) actually can be derived from the generalized Bloch-Grüneisen law for temperatures well below the Debye temperature.⁵ The first term in (1), ρ_0 , reflects the temperature independent scattering mechanisms (e.g. impurity or defect scattering) and the second term represents the contribution due to phonon scattering. Below about 100 K the phonon term is already very small as compared to ρ_0 indicating that the material is close to the residual resistance limit. Resistivity data, however, are controversial because they are strongly affected by scattering at grain boundaries, defects, and impurities. A measure of these effects may be found in the residual resistance ratio, $RRR = \rho(300K)/\rho_0$, where ρ_0 in MgB_2 is well approximated by $\rho(40K)$. A small RRR indicates a high density of defects and impurities. For MgB_2 the majority of the published data show RRR -values between 1 and 3, but larger values up to 25 have also been reported. The implications of a high defect concentration on structural, transport, and superconducting properties will be discussed in Section C. The Seebeck coefficient is far less affected by grain boundaries and impurities. Furthermore, it reflects the nature of the charge carriers at the Fermi surface more sensitively than the conductivity. The thermoelectric power, $S(T)$, of $Mg_{1-x}Al_xB_2$ is shown in Fig. 1. The inset clearly shows the decrease of T_c with Al-substitution in accordance with susceptibility²⁰ as well as resistivity data²¹. The most remarkable features of $S(T)$ are the positive sign over the whole temperature range and the linear temperature dependence from T_c to about 160 K (MgB_2). At higher temperatures $S(T)$ deviates from the straight line and tends to saturate at room temperature. The sign and the linear dependence $S \sim T$ are interpreted as the diffusion thermopower of a hole-type normal metal. The hole character of the charge carriers in MgB_2 was also seen in the positive Hall number.¹⁸ Band structure calculations³ have shown that the Fermi surface consists of several hole as well as electron like sheets. At low temperatures ($T < 160$ K) the hole carriers obviously dominate the charge transport, but at higher T electron-like states add a negative contribution to $S(T)$. This may explain the deviations from the linearity above 160 K.^{21,22} Neglecting higher order corrections the diffusion thermopower, S_d , is described by the Mott formula,²³

$$S_d = \frac{\pi^2 k^2 T}{3e} \left[\frac{\partial \ln \sigma(\varepsilon)}{\partial \varepsilon} \right]_{E_F} \quad (2)$$

k denotes Boltzmann's constant, e the charge of the carriers, E_F the Fermi energy, and $\sigma(\varepsilon)$ is a conductivity-like function for carriers of energy ε . In the residual resistance region the logarithmic derivative is simply $1/E_F$,

$$S_d = \frac{\pi^2 k^2 T}{3e E_F} \quad (3)$$

For hole carriers the Fermi energy, E_F , refers to the top of the conduction band. From equation 3 and the measured slope of $S(T)$ ($dS/dT = 0.042 \mu V/K^2$ for $x = 0$) a rough estimate of E_F can be obtained, $E_F \approx 0.57$ eV. This value may be underestimated since we have not considered yet any additional contribution (e.g. phonon drag) to $S(T)$. The phonon drag effect results in a non-linear $S \sim T^3$ at low temperatures, but this is not seen in the data of Fig. 1. For metals with high defect or impurity concentration it is expected that phonon drag is diminished due to the suppression of the phonon heat current.²³ Furthermore, the accessible temperatures ($T > 40$ K) for the normal state thermoelectric power appear to be too high to reveal the true low temperature behaviour of $S(T)$. The extrapolation of the linear $S(T)$ to zero temperature yields a small negative value, a possible indication of a "hidden" phonon drag contribution. Therefore, the slope of $S(T)$ and the estimated E_F should be considered as an upper bound for the diffusion part and as a lower limit for the Fermi energy, respectively. Assuming that charge transport below 160 K is mainly due to hole carriers in the σ bands our estimate for E_F is in fair agreement with the calculated difference between the Fermi energy and the top of the σ bands, 0.9 eV.²⁴ It is more interesting to investigate the effects of electron doping (Al substitution) on $S(T)$ and T_c . According to the calculated band structure³ (within a rigid band model) the addition of electrons reduces the Fermi energy (for σ holes) and the density of states $N(E_F)$. Suzuki et al.²⁴ calculated a decrease of E_F by 17 % for $Mg_{0.9}Al_{0.1}B_2$. From the data of Fig. 1 we estimate an increase of slope

of $S(T)$ in the linear region from $0.042 \mu\text{V}/\text{K}^2$ ($x = 0$) to $0.047 \mu\text{V}/\text{K}^2$ ($x = 0.05$) and $0.050 \mu\text{V}/\text{K}^2$ ($x = 0.1$). The corresponding decrease of E_F by 16 % ($x = 0.1$) is in excellent agreement with the calculated value. The decrease of the superconducting transition temperature with Al substitution is explained as a density-of-states effect within the strong coupling BCS theory. T_c is given by the McMillan formula,

$$T_c = \frac{\omega_{\text{ln}}}{1.2} \exp \left[-\frac{1.04(1 + \lambda)}{\lambda - \mu^*(1 + 0.62\lambda)} \right] \quad (4)$$

ω_{ln} is the logarithmically averaged phonon frequency, μ^* the screened Coulomb potential and $\lambda = N(E_F) \langle I^2 \rangle / M \langle \omega^2 \rangle$ is the electron-phonon coupling constant. $\langle I^2 \rangle$ and $\langle \omega^2 \rangle$ are the average square of the electronic matrix element and the phonon frequency, respectively, and M is the atomic mass. Band structure calculations have shown that E_F of MgB_2 is right at an edge of rapidly decreasing density of states.³ The increase of the electron number (or decrease of the hole number) leads to a decrease of $N(E_F)$ and λ and, according to (4), to the observed reduction of T_c .

C. The Influence of Defects on Electronic Transport and T_c

Electrical resistivity data for MgB_2 samples reported by various groups are qualitatively well described by (1). However, huge differences in the residual resistance ratio have been reported. Whereas the RRR varies generally between 2 and 3 values as small as 1 and as large as 25 are possible. Low RRR values are an indication of a large concentration of defects and impurities and, within the BCS theory, a decrease of T_c is expected with the increase of defect density.²⁵

We have synthesized a large number of polycrystalline MgB_2 samples with RRR values between 2 and 8 (depending on the conditions of synthesis). The T_c values as function of RRR are shown in Fig. 2. Although the variance in T_c is less than 2 K there is a clear tendency of T_c increasing with RRR in accordance with similar data for A15 thin film superconductors.^{25,26} Extending the range of T_c and RRR by including available data on MgB_2 films and neutron irradiated bulk samples it was shown very recently that the Testardi correlation is fulfilled over a wider range of T_c and RRR values² and an explanation was proposed in form of a defect-induced weak localization correction to the electron-phonon coupling constant.²⁷ Further evidence for a high defect density should be found in structural parameters, e.g. an increase of the lattice constant due to defects was observed in the A15 compounds.²⁶ It is also expected that the broader distribution of (local) lattice parameters due to the presence of defects causes a broadening of x-ray peaks. This effect can be extracted from x-ray spectra and is quantitatively characterized by the microstrain, ϵ . Fig. 3 shows both, the lattice parameters a , c and ϵ as a function of RRR (a more detailed discussion is given in ref. 28). Whereas c shows the expected increase with decreasing RRR (i.e. increasing defect density) a similar clear tendency is missing in the lattice parameter a . Obviously, defects in MgB_2 mainly affect the inter-plane spacing. The microstrain is strongly increasing because of the larger (local) distortion of the lattice at the higher defect content (Fig. 3 B). The results of this Section show that the majority of the MgB_2 bulk samples and thin films (with low RRR) have a high defect concentration giving rise to the differences in T_c , RRR , and structural parameters reported by various groups in recent publications.

D. Pressure Effects on T_c : Current Understanding and Unsolved Problems

Soon after the discovery of superconductivity in MgB_2 there was the speculation⁶ that the application of pressure might enhance T_c well above 40 K similar to what has been found more than a decade ago in high T_c cuprate superconductors. Unfortunately, the first pressure experiments clearly indicated a suppression of T_c with hydrostatic pressure.^{17,19} This result was confirmed by a number of subsequent high-pressure investigations.^{29–35} Whereas all reports agree about the negative sign of dT_c/dp , the differences in the value are still a matter of discussion. T_c decreases linearly with p in the low-pressure range ($p < 2 \text{ GPa}$) with a coefficient varying between -1 K/GPa and -2 K/GPa .^{17,29–34} Experiments on MgB_2 in an extremely non-hydrostatic environment yield an even lower value (-0.3 to -0.8 K/GPa) for the pressure coefficient of T_c .^{19,35} At higher pressure ($p > 10 \text{ GPa}$) deviations from linearity become obvious.^{32–34} The order of magnitude and the sign of dT_c/dp are well explained by the strong coupling BCS theory. Calculations of the pressure effect on the band structure and the electron-phonon coupling found reasonable agreement with the experimental data.³⁶ Using equation (4) the pressure coefficient is calculated as

$$\frac{d \ln T_c}{dp} = \frac{d \ln(\omega_{\text{ln}})}{dp} + \frac{1.04\lambda(1 + 0.38\mu^*)}{[\lambda(1 - 0.62\mu^*) - \mu^*]^2} \left\{ \frac{d \ln N(E_F)}{dp} - \frac{d \ln \langle \omega^2 \rangle}{dp} \right\} \quad (5)$$

Thereby, any pressure dependence of μ^* and $\langle I^2 \rangle$ was neglected. With reasonable values for $\mu^* \approx 0.1$ and $\lambda \approx 0.7$ Loa and Syassen³⁶ found good agreement of the calculated $d\ln T_c/dp$ with the available data. It is interesting to note that both terms in the wavy brackets of (5) give a negative contribution ($N(E_F)$ decreases and the average phonon frequency increases with pressure) but the change of $\langle \omega^2 \rangle$ dominates the pressure effect.

There is an ongoing discussion about the very different values of dT_c/dp reported so far. Tomita et al.³⁰ speculated that the pressure coefficient might be sensitive to the pressure medium used in the experiments and to shear stress possibly introduced by less hydrostatic pressure conditions resulting in a larger absolute value (closer to 2 K/GPa) of dT_c/dp . Contrary to this assumption, the smallest values of $|dT_c/dp|$ have been obtained using the most non-hydrostatic media, steatite.^{19,35} It should be noted that all pressure media (except He below 0.5 GPa) freeze above T_c of MgB_2 . We have measured different MgB_2 samples at hydrostatic (He gas pressure) and quasi-hydrostatic (Fluorinert liquid) conditions and did not find a strong sensitivity of dT_c/dp to the pressure medium.^{17,31} In particular, we found different pressure coefficients for different samples under the same hydrostatic pressure conditions.³¹ No change of dT_c/dp was observed in our He gas pressure experiments in passing through the 0.5 GPa threshold above which the He freezes above T_c . However, our experiments clearly show a correlation of the pressure coefficient and the ambient pressure T_c (Fig. 4). Samples with smaller T_c tend to have a larger pressure coefficient. Additional data from literature are also included in Fig. 4 (open symbols) and support the correlation between T_c and the pressure coefficient. Based on the discussion of the previous Section the lower T_c reflects a higher degree of defects and distortions of the MgB_2 structure. Park et al.²⁷ suggested that the defects mainly cause a reduction of the electron-phonon coupling constant, λ , due to weak localization effects. One may raise the question if the same reduction of λ can also explain the observed differences in the pressure coefficient. The maximum change of T_c of about 2 K corresponds to an increase of dT_c/dp by a factor of 2 (from -1 K/GPa to -2 K/GPa, Fig. 4). Using equation (4) with reasonable parameters, $\lambda = 0.7 \dots 1$ and $\mu^* = 0.1 \dots 0.13$, we estimate that λ decreases by about 2 to 3.5 % for a 2 K drop of T_c . Using equation (5) and the estimated values for $d\ln \omega/dp \approx 0.71$ %/GPa and $d\ln \lambda/dp \approx -1.7$ %/GPa³⁶ we calculate the change of dT_c/dp if it is solely due to the decrease of λ . We find that the expected change of the pressure coefficient is negligibly small (< 1 %) for the reasonable values of λ and μ^* listed above. Therefore, the large differences of dT_c/dp observed for different MgB_2 samples and the correlation with T_c (Fig. 4) cannot be explained by the decrease of the ambient pressure λ due to defect-induced weak localization effects.²⁷ Other mechanisms have to be considered to understand the high-pressure data.

One possibility we may speculate about is an increase of defect concentration by pressure. This would give rise to an additional suppression of λ and T_c with pressure. The effect could be small for samples with higher T_c (or lower initial defect density) but larger for "poor" samples with a high defect concentration at ambient conditions. In fact, recent experiments have shown that application of high pressure may even irreversibly change the superconducting properties, particularly T_c .³⁷ Careful structural characterization of MgB_2 at high pressure should give additional insight into the role of defects and how they are affected by external pressure.

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¹ Nagamatsu, J., Nakagawa, N., Muranaka, T., Zenitani, Y., and Akimitsu, J. (2001) Superconductivity at 39 K in magnesium diboride, *Nature* 410, 63.

² Bueza C. and Yamashita T. (2001) Review of superconducting properties of MgB_2 , preprint cond-mat/0108265, August 26.

³ Kortus, J., Mazin, I. I., Belashenko, K. D., Antropov, V. P., and Boyer, L. L. (2001) Superconductivity of metallic boron in MgB_2 , *Phys. Rev. Letters* 86, 4656.

⁴ Finnemore, D. K., Ostenson, J. E., Bud'ko, S. L., Lapertot, G., and Canfield, P. C. (2001) Thermodynamic and transport properties of superconducting $Mg^{10}B_2$, *Phys. Rev. Letters* 86, 2420.

⁵ Kong, Y., Dolgov, O. V., Jepsen, O., and Andersen, O. K. (2001) Electron-phonon interaction in the normal and superconducting states of MgB_2 , preprint cond-mat/0102499 February 27.

- ⁶ Hirsch, J. E. (2001) Hole superconductivity in MgB_2 : a high T_c cuprate without Cu, *Physics Letters A* 282, 392.
- ⁷ Bud'ko, S. L., Lapertot, G., Petrovic, C., Cunningham, C. E., Anderson, N., and Canfield, P. C. (2001) Boron isotope effect in superconducting MgB_2 , *Phys. Rev. Letters* 86, 1877.
- ⁸ Karapetrov, G., Iavarone, M., Kwok, W. K., Crabtree, G. W., and Hinks, D. G. (2001) Scanning tunnelling spectroscopy in MgB_2 , *Phys. Rev. Letters* 86, 4374.
- ⁹ Sharoni, A., Felner, I., Millo, O. (2001) Tunneling spectroscopic measurements of the superconductor gap parameter of MgB_2 , *Phys. Rev. B* 63, 220508.
- ¹⁰ Schmidt, H., Zasadzinski, J. F., Gray, K. E., Hinks, D. G. (2001) Energy gap from tunnelling and metallic Sharvin contacts onto MgB_2 : Evidence for a weakened surface layer, *Phys. Rev. B* 63, 220504.
- ¹¹ Wang, Y., Plackowski, T., and Junod, A. (2001) Specific heat in the superconducting and normal state (2-300 K, 0-16 T), and magnetic susceptibility of the 38 K superconductor MgB_2 : evidence for a multicomponent gap, *Physica C* 355, 179.
- ¹² Osborn, R., Goremychkin, E. A., Kolesnikov, A. I., and Hinks, D. G. (2001) Phonon density-of-states in MgB_2 , *Phys. Rev. Letters* 87, 017005.
- ¹³ An, J. M. and Pickett, W. E. (2001) Superconductivity of MgB_2 : Covalent bonds driven metallic, *Phys. Rev. Letters* 86, 4366.
- ¹⁴ Kong, Y., Dolgov, O. V., Jepsen, O., and Andersen, O. K. (2001) Electron-phonon interaction in the normal and superconducting states of MgB_2 , *Phys. Rev. B* 64, 020501.
- ¹⁵ Yildirim, T., Gulseren, O., Lynn, J. W., Brown, C. M., Udovic, T. J., Qing, H. Z., Rogado, N., Regan, K. A., Hayward, M. A., Slusky, J. S., He, T., Haas, M. K., Khalifah, P., Inumaru, K., and Cava, R. J. (2001) Giant anharmonicity and non-linear electron-phonon coupling in MgB_2 : A combined first-principles calculations and neutron scattering study, *Phys. Rev. Letters* 87, 037001.
- ¹⁶ Bohnen, K.-P., Heid, R., and Renker, B. (2001) Phonon dispersion and electron-phonon coupling in MgB_2 and AlB_2 , *Phys. Rev. Letters* 86, 5771.
- ¹⁷ Lorenz, B., Meng, R. L., and Chu, C. W. (2001) High pressure study on MgB_2 , *Phys. Rev. B* 64, 012507.
- ¹⁸ Kang, W. N., Jung, C. U., Kim, K. H. P., Park, M. S., Lee, S. Y., Kim, H. J., Choi, E. M., Kim, M. S., and Lee, S. I. (2001) Hole carrier in MgB_2 characterized by Hall measurements, preprint cond-mat/0102313 February 20.
- ¹⁹ Monteverde, M., Nunez-Regueiro, M., Rogado, N., Regan, K. A., Hayward, M. A., He, T., Loureiro, S. M., and Cava, R. J. (2001) Pressure dependence of the superconducting transition temperature of magnesium diboride, *Science* 292, 75.
- ²⁰ Slusky, J. S., Rogado, N., Regan, K. A., Hayward, M. A., Khalifah, P., He, T., Inumaru, K., Loureiro, S., Haas, M. K., Zandbergen, H. W., and Cava, R. J. (2001) Loss of superconductivity with the addition of Al to MgB_2 and a structural transition in $Mg_{1-x}Al_xB_2$, *Nature (London)* 410, 343.
- ²¹ Lorenz, B., Meng, R. L., Xue, Y. Y., and Chu, C. W. (2001) Thermoelectric power and transport properties of $Mg_{1-x}Al_xB_2$, *Phys. Rev. B* 64, 052513.
- ²² Muranaka, T., Akimitsu, J., and Sera, M. (2001) Thermal transport properties of MgB_2 , *Phys. Rev. B* 64, 020505.
- ²³ Blatt, F. J., Schroeder, P. A., and Foiles, C. L. (1976) Thermoelectric power of metals, Plenum Press, New York.
- ²⁴ Suzuki, S., Higai, S., and Nakao, K. (2001) Two-dimensional sigma-hole systems in boron layers: A first principles study on $Mg_{1-x}Na_xB_2$ and $Mg_{1-x}Al_xB_2$, preprint cond-mat/0102484 February 27
- ²⁵ Testardi, L. R., Meek, R. L., Poate, J. M., Royer, W. A., Storm, A. R., and Wernick, J. H. (1975) Preparation and analysis of superconducting Nb-Ge films, *Phys. Rev. B* 11, 4304.
- ²⁶ Poate, J. M., Testardi, L. R., Storm, A. R., and Augustyniak, W. M. (1975) 4He -induced damage in superconducting Nb-Ge films, *Phys. Rev. Letters* 35, 1290.
- ²⁷ Park, M. A., Savran, K., and Kim, Y. J. (2001) A new method of probing the phonon mechanism in superconductors, including MgB_2 , *Supercond. Sci. Technol.* 14, L31.
- ²⁸ Xue, Y. Y., Meng, R. L., Lorenz, B., Meen, J. K., Sun, Y. Y., and Chu, C. W. (2001) Nonstoichiometry, defects and transport properties in MgB_2 , preprint cond-mat/0105478 May 24.
- ²⁹ Saito, E., Takenobu, T., Ito, T., Iwasa, Y., Prassides, K., and Arima, T. (2001) Pressure dependence of T_c in the MgB_2 superconductor as probed by resistivity measurements, *J. Phys. Cond. Matter* 13 L267.
- ³⁰ Tomita, T., Hamlin, J. J., Schilling, J. S., Hinks, D. G., and Jorgensen, J. D. (2001) Dependence of T_c on hydrostatic pressure in superconducting MgB_2 , *Phys. Rev. B* 64, 092505.
- ³¹ Lorenz, B., Meng, R. L., and Chu, C. W. (2001) Hydrostatic pressure effect on the superconducting transition temperature of MgB_2 , preprint cond-mat/0104303 April 17.
- ³² Tissen, V. G., Nefedova, M. V., Kolesnikov, N. N., and Kulakov, M. P. (2001) Effect of pressure on the superconducting T_c of MgB_2 , preprint cond-mat/0105475 May 24.
- ³³ Deemyad, S., Schilling, J. S., Jorgensen, J. D., and Hinks, D. G. (2001) Dependence of the superconducting transition temperature of MgB_2 on pressure to 20 GPa, preprint cond-mat/0106057 June 5.
- ³⁴ Goncharov, A. F., Struzhkin, V. V., Gregoryanz, E., Mao, H. K., Hemley, R. J., Lapertot, G., Bud'ko, S. L., Canfield, P. C., and Mazin, I. I. (2001) Pressure dependence of the Raman spectrum, lattice parameters and superconducting critical temperature of MgB_2 , preprint cond-mat/0106258 June 13.
- ³⁵ Bordet, P., Mezouar, M., Nunez-Regueiro, N., Monteverde, M., Nunez-Regueiro, M. D., Rogado, N., Regan, K. A., Hayward, M. A., He, T., Loureiro, S. M., and Cava, R. J. (2001) Absence of a structural transition up to 40 GPa in MgB_2 and the

relevance of magnesium non-stoichiometry, preprint cond-mat/0106585 June 28.

- ³⁶ Loa, I. and Syassen, K. (2001) Calculated elastic and electronic properties of MgB_2 at high pressures, Solid State Commun. 118, 575.
- ³⁷ Schlachter, S. I., Fietz, W. H., Grube, K., and Goldacker, W. (2001) High pressure studies of T_c and lattice parameters of MgB_2 , preprint cond-mat/0107205 July 10.

FIG. 1. Seebeck coefficient of $Mg_{1-x}Al_xB_2$. The curves for different x are offset by a constant and the zero values are indicated by short horizontal lines

FIG. 2. T_c of various MgB_2 samples as function of the residual resistance ratio. The line is a guide to the eye reflecting the Testardi correlation over a wider range of T_c and RRR .

FIG. 3. Lattice constants (A) and micro strain (B) of MgB_2 as function of the residual resistance ratio.

FIG. 4. Pressure coefficient as function of T_c . Open circles are literature data from ref. 29, 30, 32, 33.







